	Hits	Search Text	DBs	Time
$\vdash$	11113	Oddicii Text		Stamp
1	697	("257/347-348").CCLS.	USPAT	2001/ 10/03
				21:46
2	1937	(("257/347-348,351,369") or	USPAT	2001/ 10/03
L		("438/353,149")).CCLS.		21:46
İ		(((((((eib not protein) not eib-n\$8.in.) not		
3	120	eib.in.) not eib adj et adj al) not nicholas adj4 eib) not (536/23.2 536/23.6	USPAT; US-PGPUB; EPO; JPO;	2001/
٦		536/24.5 435/419 435/468 435/252.3	DERWENT; IBM TDB	10/03 12:01
		800/298 800/286).ccls.) not erasure) not encoder.adj.inbound).not.eib.adj.lan		
Γ.	Ī.,,,		USPAT; US-PGPUB; EPO; JPO;	2001/
4	198	eib not protein	DERWENT; IBM TDB	10/03 11:44
	Ī		USPAT; US-PGPUB; EPO; JPO;	2001/
5	251	eib	DERWENT; IBM TDB	10/03 11:42
$\vdash$	<b>†</b>	<u> </u>		2001/
6	107	body adj effect and soi	USPAT	01/31
$\vdash$	<del> </del>	•		08:00 2001/
7	104	depletion adj region WITH mos	USPAT	01/30
$\vdash$	<del> </del>	<u> </u>		18:10 2001/
8	3660	depletion adj region	USPAT	01/30
⊢	<del> </del>	<b>.</b>		18:09
9	188	((("257/347-348").CCLS.) and (mos oxide))	USPAT	2001/ 01/30
	<b></b>	and (bias threshold) and charge		17:09
10	379	((("257/347-348").CCLS.) and (mos oxide))	USPAT	2001/ 01/30
	ļ	and (bias threshold)	······································	17:08
1,1	19	"Dynamic threshold voltage mosfet"	USPAT	2001/ 01/30
Ľ				15:33
12	362	accumulation adj mode	USPAT	2001/
'2	302	accumulation auj mode	OGFAT	01/30 15:33
Г.,	Ī.,	/		2001/
13	62	(accumulation adj mode) and mosfet	USPAT	01/30 15:33
		((("257/347-348").CCLS.) and (mos oxide))		2001/
14	23	and (bias threshold) and standby	USPAT	01/30 09:59
	1			2001/
15	1	("5559368").PN.	USPAT	01/30 09:56
-		<u> </u>		2001/
16	1	("5616944").PN.	USPAT	01/30
		•		09:49 2001/
17	848	nfet	USPAT	01/29
	<del> </del>	! !		18:04 2001/
18	172	hiroo.in. and masuda.in.	JP0	01/29
_				17:35 2001/
19	1	hiroo.in. and masuda.in.	DERWENT	01/29
<u> </u>			***************************************	17:34 2001/
20	32	((hiroo).in) and masuda.in.	USPAT	01/29
				17:32
21	0	((hiroo).in) and masudo.in.	USPAT	2001/
	<b></b>			17:31
22	0	(((hiroo).in) and masuda.in.) and tsunemo.in.	USPAT	2001/ 01/29
				17:31
23	1335	(hiroo).in	USPAT	2001/ 01/29
				17:30
24	0	"variable threshold voltage mosfet"	USPAT	2001/
24		valuable threshold voltage mostet		01/29 16:58
25	48	vimas	LICPAT	2001/
25	<b>→</b> 0	vtmos	3	01/29 16:07
00		((("257/347-348").CCLS.) and (mos oxide))		2001/
26	11	and (dynamic adj threshold)	USPAT	01/29 16:06
		((("257/347-348").CCLS.) and (mos oxide))		2001/
27	0	and (dynamic adj. threshold near mos)	USPAT	01/29
		((("257/347-348").CCLS.) and (mos oxide))		15:36 2001/
28	7	and (bias threshold) and accumulation adj		01/29
	L	mode		15:34

	Hits	Search Text	DBs	Time
<del> </del>	<del> </del>	((("257/347-348").CCLS.) and (mos oxide))		Stamp 2001/
29	7	and (bias threshold) and "accumulation	USPAT	01/29
		mode"	1	15:29
	1		<u> </u>	2001/
30	1	"5359219".PN.	USPAT	01/29
<u></u>	<u> </u>			15:16
31	1	"5641980".PN.		2001/
			USPAT	01/29
				15:15
32	1	"5923067".PN.	USPAT	2001/
				01/29
├—	<b>-</b>	: 	ļ	15:15
33	1	"5294821".PN.	USPAT	2001/
				01/29
$\vdash$	†·····	<u> </u>		15:15
34	1	"5923067".PN.	USPAT	2001/ 01/29
		!		15:13
	<b>†</b>	<u> </u>		2001/
35	1	"5892256".PN.	USPAT	01/29
	l			14:21
	T		***************************************	2001/
36	1	"5945712".PN.	USPAT	01/29
	ļ			14:21
	1	"6072217".PN.	USPAT	2001/
37				01/29
<u> </u>				14:21
38	1	*5608252*.PN.	USPAT	2001/
				01/29
	654	(("257/347-348").CCLS.) and (mos oxide)	USPAT	14:20
39				2001/ 01/29
33				13:58
40	53	accumulation adj mode and 257/3\$2.ccls.	USPAT	2001/
				01/29
				12:18
				2001/
41	26	dtmos	USPAT	01/29
				11:58
	0	electrically adj induced adj body	USPAT	2001/
42				01/29
			***************************************	09:37
				2001/
43	48	vtmos	USPAT	01/29
		***************************************		09:36
44	91	eib	USPAT	2001/
44	91	eiD	USPAT	01/29
_	0	eib-mos	USPAT	09:06
45				2001/ 01/29
-5				09:06
	0	eib and vtmos and 257/\$3.ccls.	USPAT	2001/
46				01/29
				09:01
	0	eib and vtmos	USPAT	2001/
47				01/29
				09:01